

**DESCRIPTION**

This is a Silicon Phototransistor designed for applications requiring medium gain and a wide viewing angle.

**FEATURES**

- Medium Gain, typically 500 Hfe
- Sensitivity range 400-1000 nm
- High Reliability
- Hermetic Package

**ABSOLUTE MAXIMUM RATINGS**

- Storage temperature..... -55°C to +125°C
- Case operating temperature... -40°C to +85°C
- Lead solder temperature..... 260°C, 10 seconds
- Supply Voltage..... +30 Volts

**OPERATING CONDITIONS**

- Supply Voltage..... +0 to +30 Volts

**PRELIMINARY**

**OUTLINE DIMENSIONS**

All dimensions are in inches (except as noted)

Pinout : 1. Emitter, 2. Base, 3. Case (Collector)

**ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)**

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Collector Emitter Breakdown	$I_C = 100 \mu A, I_B = 0$	BVCEO	60			Volts
Emitter - Collector Breakdown	$I_E = 100 \mu A, I_B = 0$	BVECO	5			Volts
Collector Dark Current	VCE = 20V, H = 0 mW/cm <sup>2</sup>	ICEO			100	nA
Collector-Emitter Saturation	$I_C = 2 \text{ mA}, I_B = 100 \mu A$	VCESAT			0.3	Volts
Response Time	10%-90%, IC = 1 mA VCE = 5 V, RL = 1000 Ω	t <sub>r</sub>		15		μsec
		t <sub>f</sub>		15		μsec
Current Gain	IC = 2 mA, VCE = 5 V	H <sub>fe</sub>	200	500		

distributed by